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(71) Applicant *(for all designated States except US)*: **SAINT-GOBAIN CERAMICS & PLASTICS, INC.** [US/US]; One New Bond Street, Worcester, Massachusetts 01615-0138 (US).

(72) Inventors: **NARENDAR, Yeshwanth**; 34 Carlisle Road, Westford, Massachusetts 01886 (US). **BUCKLEY, Richard, F.**; 8 Comstock Drive, Shrewsbury, Massachusetts 01545 (US).

(74) Agents: **LARSON NEWMAN ABEL & POLANSKY, LLP** et al.; 5914 West Courtyard Drive, Suite 200, Austin, TX 78730 (US).

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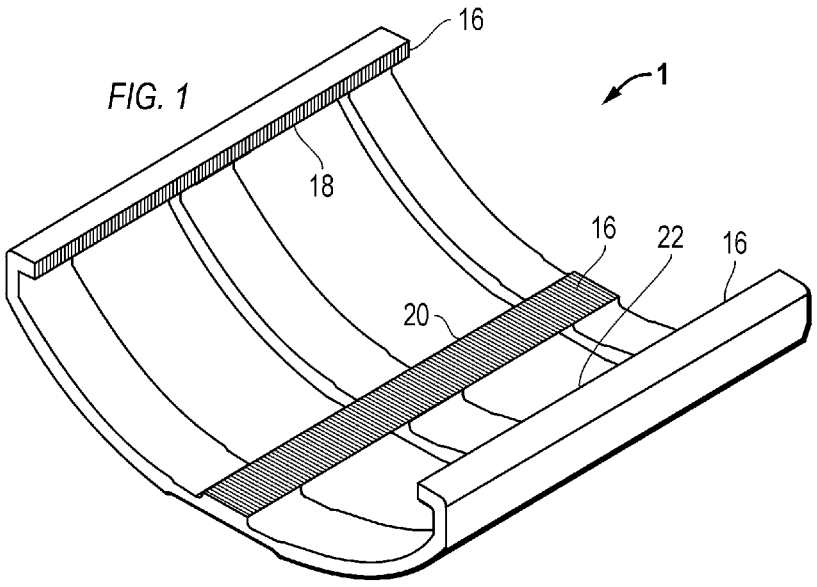
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(57) Abstract: A semiconductor processing component has an outer surface portion comprised of silicon carbide, the outer surface portion having a skin impurity level and a bulk impurity level. The skin impurity level is average impurity level from 0 nm to 100 nm of depth into the outer surface portion, the bulk impurity level is measured at a depth of at least 3 microns into the outer surface portion, and the skin impurity level is not greater than 80% of the bulk impurity level

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